Elektronische Bauelemente

EMT1

Dual PNP
Plastic-Encapsulated Transistors

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Mounting Possible With SOT-563 Automatic Mounting Machines.
- Transistor elements are independent, eliminating interference.

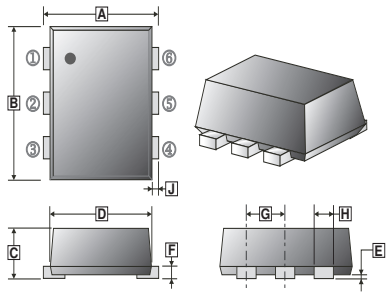
MARKING

T1

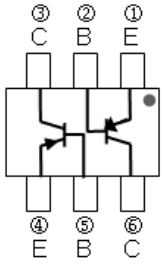
PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-563	3K	7 inch

SOT-563



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.50	1.70	F	0.09	0.16
B	1.50	1.70	G	0.45	0.55
C	0.525	0.600	H	0.17	0.27
D	1.10	1.30	J	0.10	0.30
E	0.05 REF.				



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current – Continuous	I_C	-150	mA
Collector Power Dissipation	P_C	150	mW
Junction & Storage temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60	-	-	V	I_C= -50μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-50	-	-	V	I_C= -1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-	-	V	I_E= -50μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	-0.1	μA	V_{CB}= -60V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	-0.1	μA	V_{EB}= -7V, I_C=0
DC Current Gain	h_{FE}	120	-	560		V_{CE}= -6V, I_C= -1mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	-0.5	V	I_C= -50mA, I_B= -5mA
Transition Frequency	f_T	-	140	-	MHz	V_{CE}= -12V, I_C= -2mA, f=100MHz
Collector Output Capacitance	C_{ob}	-	-	5	pF	V_{CB}= -12V, I_E=0, f=1MHz